



제 30회 한국반도체학술대회

The 30th Korean Conference on Semiconductors

2023년 2월 13일(월)~ 15일(수) | 강원도 하이원리조트(그랜드호텔 컨벤션타워)

2023년 2월 15일(수), 16:00-17:45

Room B (에메랄드 II+III, 5층)

D. Thin Film Process Technology 분과

[WB3-D] Area-selective Deposition

좌장: 김우희 교수(한양대학교), 오일권 교수(아주대학교)

<p>WB3-D-1 16:00-16:30 [초청]</p>	<p>Precursor Choice of Metal Oxides in Atomic Layer Deposition Il-Kwon Oh <i>Department of Electrical and Computer Engineering, Ajou University</i></p>
<p>WB3-D-2 16:30-16:45</p>	<p>Selective Etching Reactions during Atomic Layer Deposition of Indium Gallium Zinc Oxide Iaen Cho¹, Jae Hoon Cho², Jae Kyeong Jeong², and Bonggeun Shong¹ ¹<i>Department of Chemical Engineering, Hongik University, </i>²<i>Department of Electronic Engineering, Hanyang University</i></p>
<p>WB3-D-3 16:45-17:00</p>	<p>Area Selective Deposition Using Ruthenium Precursor Inhibitor and Control of Inhibitor Packing Density Chi Thang Nguyen¹, Eun-Hyoung Cho², Ngoc Le Trinh¹, Bonwook Gu¹, Mingyu Lee¹, and Han-Bo-Ram Lee¹ ¹<i>Department of Materials Science and Engineering, Incheon National University, </i>²<i>Beyond Silicon Lab, Samsung Advanced Institute of Technology</i></p>
<p>WB3-D-4 17:00-17:15</p>	<p>Area-Selective Atomic Layer Deposition of Ru Thin Films Using Aldehyde-Based Inhibitors on Nitride Surfaces Jinseon Lee and Woo-Hee Kim <i>Department of Materials Science and Chemical Engineering, Hanyang University</i></p>
<p>WB3-D-5 17:15-17:30</p>	<p>Demonstrations on Synaptic Operations of In-Ga-Zn-O Thin Film Transistor Using Solution-Process Li-doped ZrO₂ Electrolyte Gate Insulator Dong-Hee Kim¹, Young-Ha Kwon², Nak-Jin Seong², Kyu-Jeong Choi², and Sung-Min Yoon¹ ¹<i>Kyung Hee University, </i>²<i>NCD Co., Ltd.</i></p>
<p>WB3-D-6 17:30-17:45</p>	<p>Thiol Instigated Area Selective Deposition of HfO₂ ALD on Copper, Silicon Oxide and Titanium Nitride Substrates Summal Zoha¹, Bonwook Gu¹, Zunair Masroor¹, Fabian Pieck², Ralf Tonner², and Han-Bo-Ram Lee¹ ¹<i>Department of Materials Science and Engineering, Incheon National University, </i>²<i>Wilhelm Ostwald Institute for Physical and Theoretical Chemistry, University of Leipzig</i></p>